

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☒ Advanced trench cell design
- ☒ Low Thermal Impedance
- ☒ Fast Switching Speed
- ☒ 100% Avalanche Tested

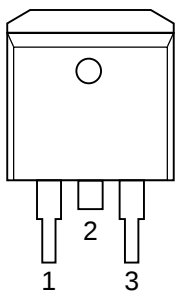
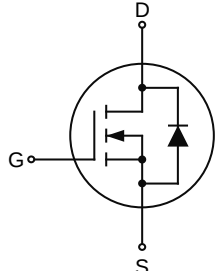
1.2 Applications

- ☒ DC/DC Conversion
- ☒ Power Switch
- ☒ Motor Drives
- ☒ Battery management

1.3 Quick reference

- ☒ $BV \geq 100\text{ V}$
- ☒ $P_D \leq 250\text{ W}$
- ☒ $I_D \leq 180\text{ A}$
- ☒ $R_{DS(ON)} \leq 2.7\text{ m}\Omega @ V_{GS} = 10\text{ V}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate(G)	 Top View TO-263	
2	Drain(D)		
3	Source(S)		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C=25^{\circ}\text{C}$	100	-	V
V_{GS}	Gate-Source Voltage	$T_C=25^{\circ}\text{C}$	-	± 20	V
I_D^{***}	Drain Current (DC)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	180	A
$I_{DM}^{*,***}$	Drain Current (Pulsed)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	720	A
P_D	Drain Power Dissipation	$T_C=25^{\circ}\text{C}$	-	250	W
E_{AS}	Single Pulsed Avalanche Energy	$V_{DD}=50\text{ V}, L=0.3\text{ mH}$	-	911	mJ
T_J, T_{stg}	Operating Junction and Storage Temperature Range		-55	150	$^{\circ}\text{C}$
$R_{\theta JA}^{**}$	Thermal Resistance-Junction to Ambient		-	40	$^{\circ}\text{C/W}$
$R_{\theta JC}^{**}$	Thermal Resistance-Junction to Case		-	0.5	

Notes:

* Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

** Surface Mounted on 1 in² pad area, $t \leq 10\text{ sec}$.

*** Limited by bonding wire.

4. Marking Information

Product Name	Marking
KJ028N10DA	KJ028N10A YWWXXX YWWXXX: Date Code

5. Ordering Code

Product Name	Package	Reel size	Tape width	Quantity (pcs)
KJ028N10DA	TO-263	13"	24 mm	800

Note: KUAJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C).

6. Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _{DS} =250 μA	100	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250 μA	2	-	4	V
I _{DSS}	Drain Leakage Current	V _{DS} =100 V, V _{GS} =0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{DS} =0 V, V _{GS} =±20 V	-	-	±100	nA
R _{DS(ON)} ^a	On-State Resistance	V _{GS} =10 V, I _{DS} =75 A	-	2.3	2.7	mΩ
g _{FS}	Forward Transconductance	V _{GS} =5 V, I _{DS} =75 A	-	150	-	S
R _g	Gate Resistance	Frequency=1 MHz	-	1.3	-	Ω
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	V _{GS} =0 V, I _{SD} =75 A, V _{GS} =0 V	-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{DD} =50 V, V _{GS} =0 V, I _{SD} =75 A, diF/dt=100 A/μs	-	66	-	ns
Q _{rr}	Reverse Recovery Charge		-	129	-	nC
Dynamic Characteristics ^b						
C _{iSS}	Input Capacitance	V _{DS} =50 V, V _{GS} =0 V, f=1.0 MHz	-	8508	-	pF
C _{oSS}	Output Capacitance		-	1105	-	
C _{rSS}	Reverse Transfer Capacitance		-	44	-	
t _{d(on)}	Turn-on Delay Time	V _{DD} =50 V, V _{GS} =10 V, I _D =75 A, R _{GEN} =6 Ω	-	68	-	ns
t _r	Turn-on Rise Time		-	74	-	
t _{d(off)}	Turn-off Delay Time		-	96	-	
t _f	Turn-off Fall Time		-	39	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =50 V, V _{GS} =10 V, I _D =75 A	-	140	-	nC
Q _{gs}	Gate-Source Charge		-	42	-	
Q _{gd}	Gate-Drain Charge		-	41	-	

Notes:

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

7. Typical Characteristics

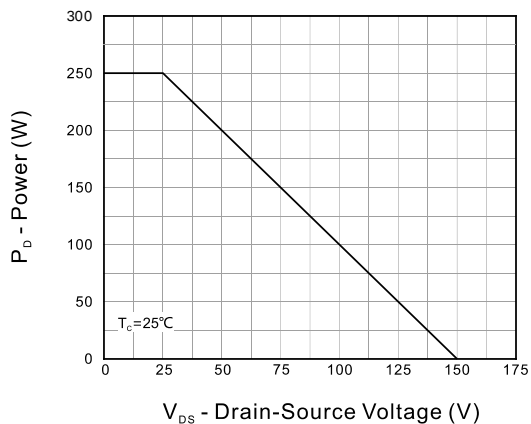


Fig 1. Output Characteristics

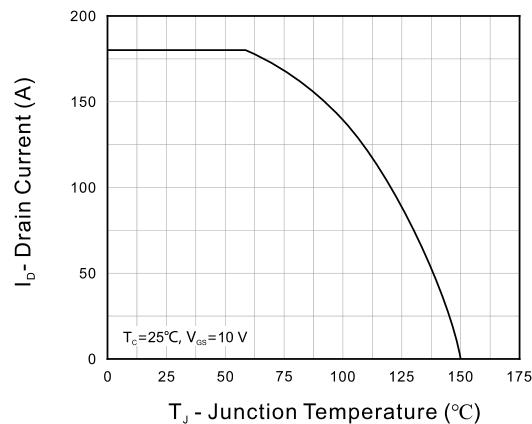


Fig 2. Current Capability

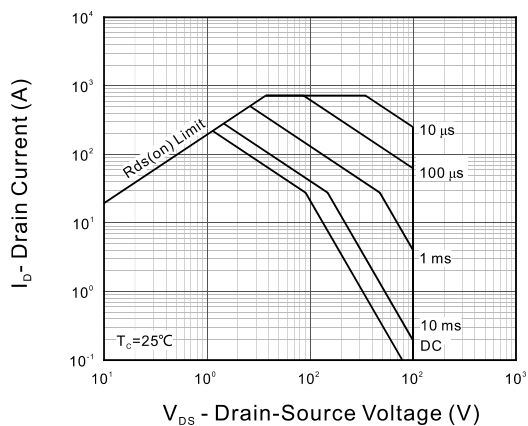


Fig 3. Safe Operation Area

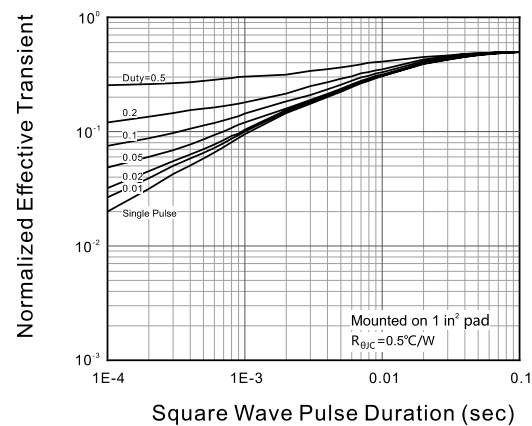


Fig 4. Transient Thermal Impedance

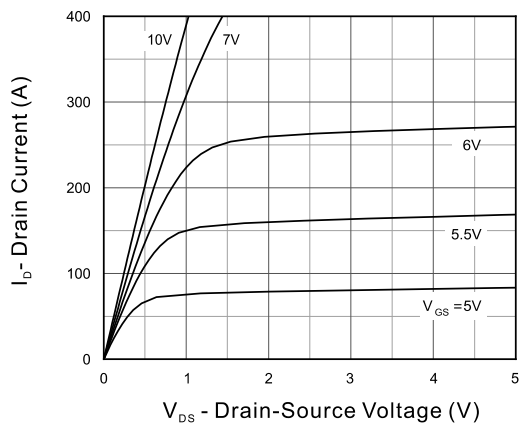


Fig 5. Output Characteristics

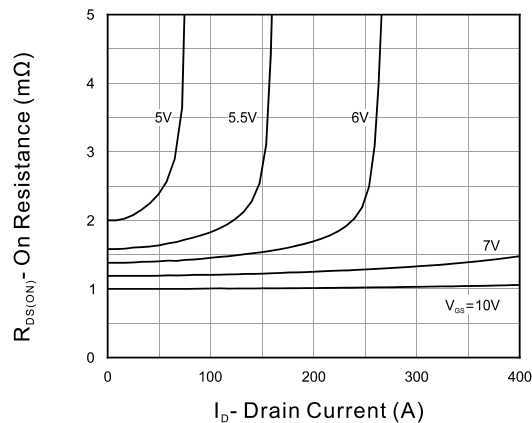


Fig 6. On Resistance

7. Typical Characteristics (cont.)

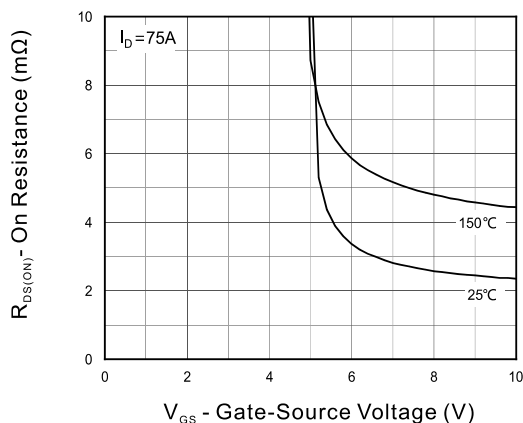


Fig 7. Transfer Characteristics

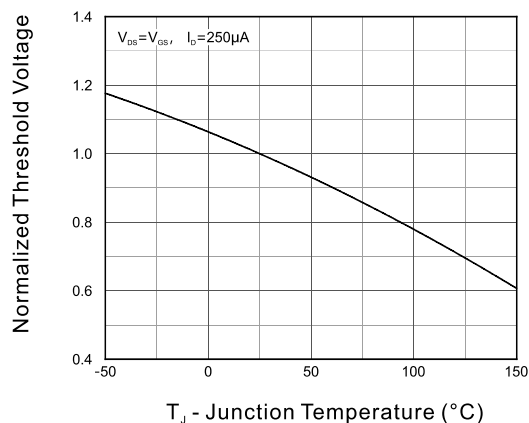


Fig 8. Normalized Threshold Voltage

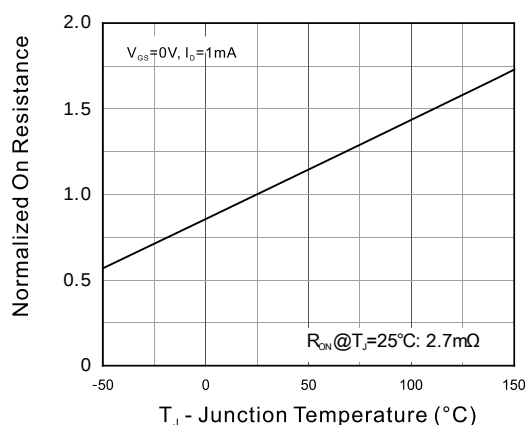


Fig 9. Normalized On Resistance

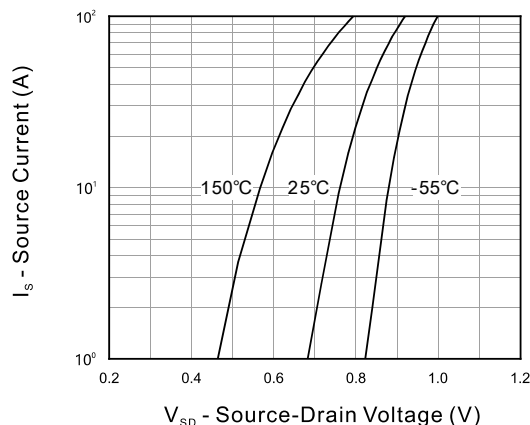


Fig 10. Diode Forward Current

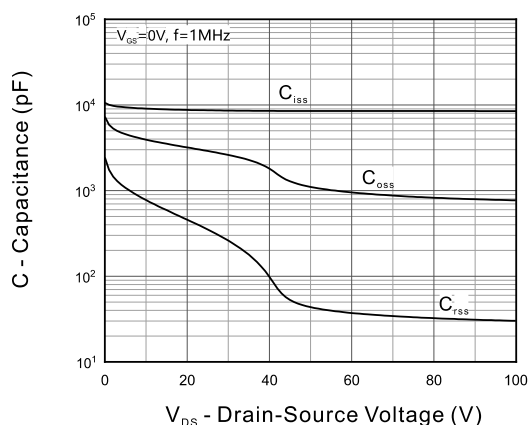


Fig 11. Capacitance

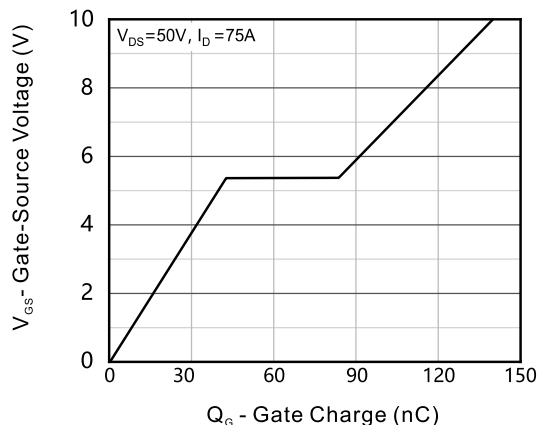
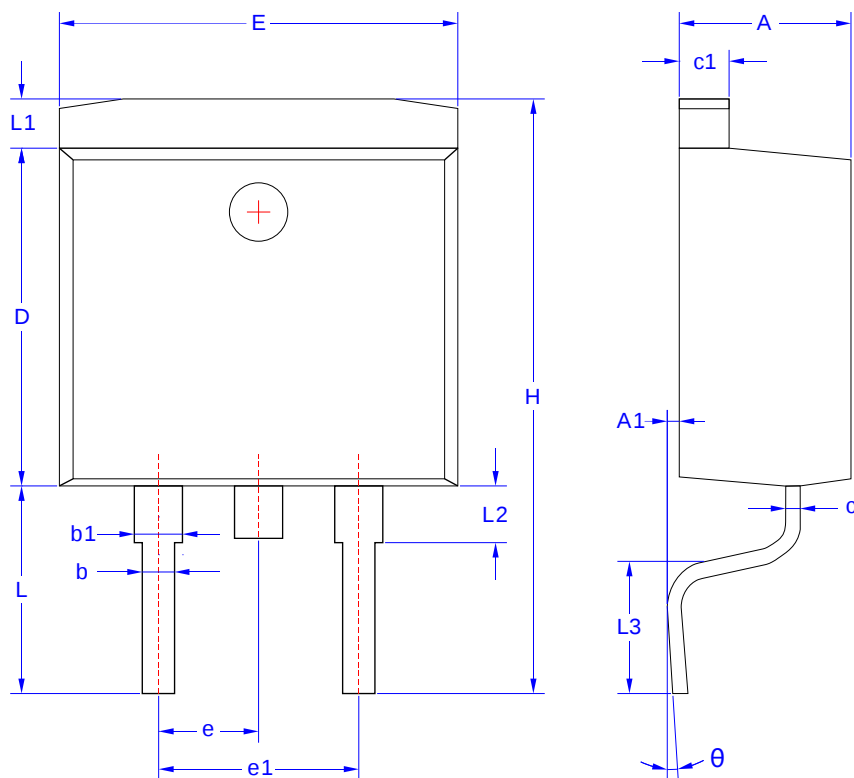


Fig 12. Gate Charge

8. Package Dimensions

TO-263 Package



Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX
A	4.470	-	4.670
A1	0.000	-	0.150
b	0.710	-	0.910
b1	1.170	-	1.370
c	0.310	-	0.530
c1	1.170	-	1.370
D	8.500	-	8.900
E	10.01	-	10.31
e	2.540 BSC		
e1	4.980	-	5.180
H	14.940	-	15.500
L	4.950	-	5.450
L1	1.120	-	1.420
L2	1.300	-	1.700
L3	2.340	-	2.740
θ	0°	-	8°